

TRANSISTOR MOS-FET IGBT DIODE

$\Delta V_{BE}/\Delta V_{DS}/\Delta V_{GE}/\Delta V_{CE}/\Delta V_F$ TESTER 過渡熱抵抗測定器

DVFN240BS 200V 40A



●DVFN240BS is the high accuracy thermal resistance tester which can measure V_{F1} and ΔV_F with 0.1mV accuracy. Power time is 99.9 sec maximum at 100W.

●DVFN240BSは V_{F1} と ΔV_F を0.1mV精度で測定可能な高精度熱抵抗テスターです。また、パワータイムは100Wで最大99.9secを持っています。

MODEL	DVFN240BS	
MEASUREMENT RANGE	B-E OPEN/SHORT	
PRE-TEST	$V_{BE1}/V_{DS1}/V_{CE1}/V_{F1}$	0000.0mV~3200.0mV
	$\Delta V_{BE}/\Delta V_{DS}/\Delta V_{CE}/\Delta V_F$	000.0mV~999.9mV
SETTING RANGE		
MEASURABLE DEVICES	NPN/PNP, N/P-MOS FET, N/P-DIODE, N/P-IGBT(GE), N/P-IGBT(CE)	
V_{CB}/V_{DS}	1V~199V	
I_E/I_D	0.01A~39.99A(10mA STEP)	
IM	1mA~99mA	
POWER FORCING TIME(PT)	100 μ s~99.9s	
DELAY TIME(DT)	10 μ s~999 μ s	
GATE LIMIT(GL)	1.0V~19.9V	
LOWER GATE(LG)/UPPER GATE(UG)	000.0mV~999.9mV	
BINNING		
OPEN/SHORT CHECK	$V_{F1} > 3V$...OPEN	$V_{F1} < 0.2V$...SHORT
BIN INDICATION	PASS, LOW, HIGH, AVAL, REJECT	
DIMENSIONS & WEIGHT		
MAIN UNIT	430(W) \times 700(D) \times 245(H)...44kg	
POWER UNIT	430(W) \times 700(D) \times 245(H)...47kg	

Forcing Power Range Diagram

